

2SB1393, 2SB1393A

Silicon PNP epitaxial planar type

For power amplification

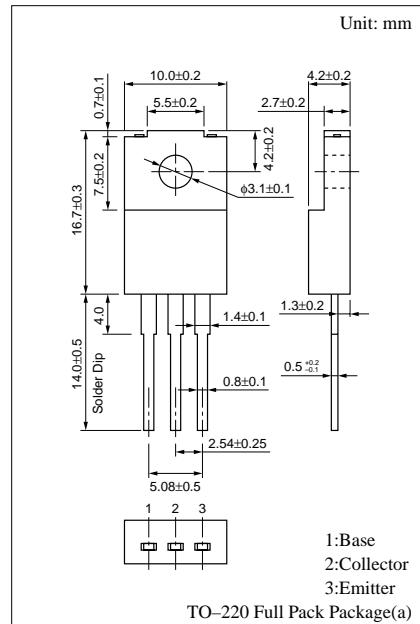
Complementary to 2SD1985 and 2SD1985A

■ Features

- Satisfactory linearity of forward current transfer ratio h_{FE}
- Low collector to emitter saturation voltage $V_{CE(sat)}$
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings ($T_C=25^\circ C$)

| Parameter | | Symbol | Ratings | Unit |
|------------------------------|------------------|-----------|-------------|------------|
| Collector to base voltage | 2SB1393 | V_{CBO} | -60 | V |
| | 2SB1393A | | -80 | |
| Collector to emitter voltage | 2SB1393 | V_{CEO} | -60 | V |
| | 2SB1393A | | -80 | |
| Emitter to base voltage | | V_{EBO} | -5 | V |
| Peak collector current | | I_{CP} | -5 | A |
| Collector current | | I_C | -3 | A |
| Collector power dissipation | $T_C=25^\circ C$ | P_C | 25 | W |
| | $T_a=25^\circ C$ | | 2.0 | |
| Junction temperature | | T_j | 150 | $^\circ C$ |
| Storage temperature | | T_{stg} | -55 to +150 | $^\circ C$ |



■ Electrical Characteristics ($T_C=25^\circ C$)

| Parameter | | Symbol | Conditions | min | typ | max | Unit |
|---|----------|---------------|---|-----|-----|------|---------|
| Collector cutoff current | 2SB1393 | I_{CEO} | $V_{CE} = -30V, I_B = 0$ | | | -300 | μA |
| | 2SB1393A | | $V_{CE} = -60V, I_B = 0$ | | | -300 | |
| Collector cutoff current | 2SB1393 | I_{CES} | $V_{CE} = -60V, V_{BE} = 0$ | | | -200 | μA |
| | 2SB1393A | | $V_{CE} = -80V, V_{BE} = 0$ | | | -200 | |
| Emitter cutoff current | | I_{EBO} | $V_{EB} = -5V, I_C = 0$ | | | -1 | mA |
| Collector to emitter voltage | 2SB1393 | V_{CEO} | $I_C = -30mA, I_B = 0$ | -60 | | | V |
| | 2SB1393A | | | -80 | | | |
| Forward current transfer ratio | | h_{FE1}^* | $V_{CE} = -4V, I_C = -1A$ | 70 | | 250 | |
| | | | $V_{CE} = -4V, I_C = -3A$ | 10 | | | |
| Base to emitter voltage | | V_{BE} | $V_{CE} = -4V, I_C = -3A$ | | | -1.8 | V |
| Collector to emitter saturation voltage | | $V_{CE(sat)}$ | $I_C = -3A, I_B = -0.375A$ | | | -1.2 | V |
| Transition frequency | | f_T | $V_{CE} = -5V, I_C = -0.1A, f = 1MHz$ | 20 | | | MHz |
| Turn-on time | | t_{on} | $I_C = -1A, I_{B1} = -0.1A, I_{B2} = 0.1A, V_{CC} = -50V$ | 0.5 | | | μs |
| Storage time | | t_{stg} | | 1.2 | | | μs |
| Fall time | | t_f | | 0.3 | | | μs |

* h_{FE1} Rank classification

| Rank | Q | P |
|-----------|-----------|------------|
| h_{FE1} | 70 to 150 | 120 to 250 |

